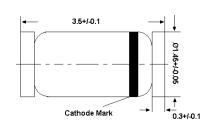
Silicon Schottky Barrier Diode

Characteristics equivalent to or better than 1N60P ideal for used in detection or for switching on the radio, TV, etc.

LL-34



Glass case MiniMELF Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	Io	50	mA
Peak Forward Current	I _{FM}	150	mA
Surge Forward Current	I _{surge}	500	mA
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1 \text{ V}$	I _F	4	-	mA
Reverse Current at $V_R = 10 \text{ V}$	I _R	-	50	μΑ
Total Capacitance At V = -1 V, f = 1 MHz	C _{tot}	-	1	pF
Rectification efficiency at Vi = 2 Vrms, R = 5 K Ω	η	55	ı	%

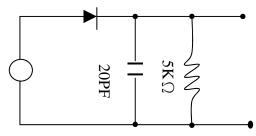






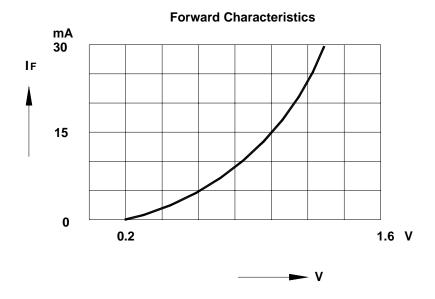


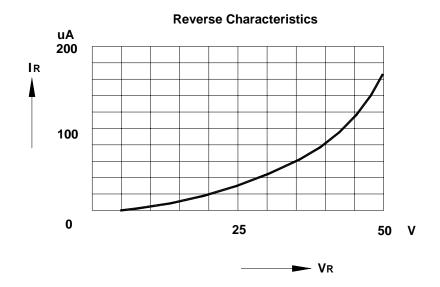




Input 2Vrms

Rectification Efficiency Measurement Circuit







SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)









